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03500.017975.

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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|---------------------------------|---|---------------------------|
| In re Application of: |) | |
| | : | Examiner: Anthony D. Fick |
| SHUNICHI ISHIHARA |) | |
| | : | Group Art Unit: 1753 |
| Application No.: 10/549,900 |) | |
| | : | |
| 371(c) Date: September 20, 2005 |) | |
| | : | |
| For: SOLAR CELL |) | December 21, 2006 |

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449. Copies of the listed documents, other than the U.S. patent documents, are enclosed.

The following documents are discussed at the following pages of the specification:

| <u>Documents</u> | <u>Page(s)</u> |
|--|----------------|
| Haruo Itoh, et al., Journal of Crystal Growth, Vol. 45, 1978 | 3, 15 |
| T. H. Wang, et al., Solar Energy Materials and Solar Cells, Vol. 41/42, 1996 | 4 |
| Japan 10-98205 | 5 |
| Japan 5-48128 | 6, 27 |
| Japan 8-250433 | 30 |
| Japan 2965094 | 33 |

According to a commercial database, U.S. Patent No. 6,387,780 is in the same patent family as Japan 10-98205, and U.S. Patent No. 5,246,886 is in the same patent family as Japan 2965094.

The Examiner's attention is also directed to the following U.S. Application:

| <u>Application No.</u> | <u>Filing Date</u> | <u>Applicants</u> |
|------------------------|--------------------|--------------------------|
| 11/501,005 | 08/09/2006 | S. Ishihara N. Kawase |

With respect to the documents cited in the September 19, 2005 Information Disclosure Statement, those documents were listed in the International Search Report and/or Written Opinion which issued in the corresponding international application. In addition, Japan 5-36611, which was cited in the September 19, 2005 Information Disclosure Statement, is discussed at pages 3, 6, and 27 of the specification.

This Information Disclosure Statement is being filed before the issuance of a first Office Action on the merits. Therefore, no fee under 37 C.F.R. § 1.97(c)(2) is believed due. Nevertheless, the Commissioner may charge Deposit Account No. 06-1205, should any fee be due for filing this paper.

Applicant requests that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be initialed and returned indicating that such information has been considered.

Applicant's undersigned attorney may be reached in our Costa Mesa, California office at (714) 540-8700. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,



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FORM PTO 1449 (modified)
 U.S. DEPARTMENT OF COMMERCE
 PATENT AND TRADEMARK OFFICE
 LIST OF REFERENCES CITED BY APPLICANT(S)
 (Use several sheets if necessary)

ATTY DOCKET NO. **03500.017975.**
 APPLICATION NO. **10/549,900**

APPLICANT **SHUNICHI ISHIHARA**

371(c) DATE **September 20, 2005**
 GROUP **1753**

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|----------------------|--------------------|----------|------------------|-------|----------|-------------------------------|
| | 6,653,554 | 11/25/03 | Ishihara | 136 | 258 | |
| | 6,387,780 | 05/14/02 | Nishida | 438 | 497 | |
| | 5,246,886 | 09/21/93 | Sakai, et al. | 437 | 228 | |
| | 2006/0194417 | 08/31/06 | Ishihara, et al. | 438 | 479 | |
| | 2005/0136576 | 06/23/05 | Ishihara, et al. | 438 | 162 | |
| | 2005/0066881 | 03/31/05 | Nakagawa, et al. | 117 | 18 | |
| | | | | | | |
| | | | | | | |
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FOREIGN PATENT DOCUMENTS

| DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION YES/NO/ OR ABSTRACT |
|--------------------|----------|---------|-------|----------|---------------------------------------|
| 2965094 | 08/13/99 | Japan | | | Abstract |
| 10-98205 | 04/14/98 | Japan | | | Abstract |
| 8-250433 | 09/27/96 | Japan | | | Abstract |
| 5-48128 | 02/26/93 | Japan | | | Abstract |
| | | | | | |

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

| | |
|--|--|
| | Haruo Itoh, et al., "Characterization of Silicon Layers Epitaxially Grown on Metallurgical-Grade Polycrystalline Substrates", Journal of Crystal Growth, Vol. 45, 1978, pp. 446-453. |
| | T. H. Wang, et al., "Growth of silicon thin layers on cast MG-Si from metal solutions for solar cells", Solar Energy Materials and Solar Cells, Vol. 41/42, 1996, pp. 19-30. |

EXAMINER _____ DATE CONSIDERED _____

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.